

### **IN THE SPECIFICATION**

On page 3, in the Brief Description of The Drawings, please insert the following sentence after the description of Figure 9:

Fig. 10 is a table of chemical formulations of surfactants.

On page 5, second paragraph, please replace the paragraph with the below amended paragraph:

Referring to Fig. 2, a bar graph is provided that indicates the pattern density effect improvements, and the barrier selectivity improvements that result from the use of various surfactant additives. The first five additives shown in Fig. 2 are non-ionic surfactants, the sixth additive is an anionic surfactant, the seventh additive is an amphoteric surfactant, and the last three additives are cationic tertiary amine salts. Detailed chemical formulations are given in ~~Table 1~~ Figure 10. In the experiments from which this data is obtained, the patterned erosion rate is measured on an SiOF patterned wafer based on a 3mm x 3mm structure with 6 micron wide metal lines, a spacing between the metal lines of 0.8 microns, and an etch depth of 6,000 angstroms. The base slurry without additive has a nearly zero (i.e., <10 angstroms per minute) blanket SiOF polish rate. This would correspond to a Cu:SiOF selectivity of > 200.